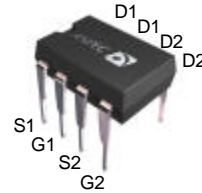


Dual N-Channel Enhancement Mode MOSFET

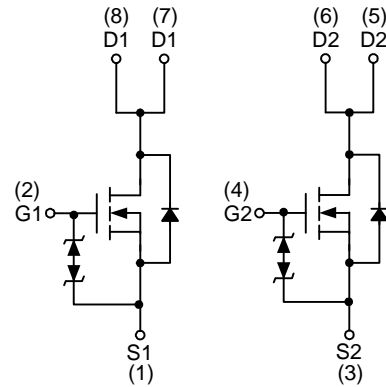
### Features

- 60V/4A,  
 $R_{DS(ON)} = 60m\Omega(\text{typ.}) @ V_{GS} = 10V$   
 $R_{DS(ON)} = 72m\Omega(\text{typ.}) @ V_{GS} = 4.5V$
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free and Green Devices are Available (RoHS Compliant)

### Pin Description



Top View of DIP-8



N-Channel MOSFET

### Applications

- Power Management in DC/DC Converter, DC/AC Inverter Systems.

### Ordering and Marking Information

<p>APM9948 □□-□□ □</p> <div style="margin-left: 20px;"> <p>└─ Assembly Material</p> <p>└─ Handling Code</p> <p>└─ Temp. Range</p> <p>└─ Package Code</p> </div>	<p>Package Code J : DIP-8</p> <p>Operating Junction Temp. Range C : -55 to 150 °C</p> <p>Handling Code TU : Tube</p> <p>Assembly Material L : Lead Free Device G : Halogen and Lead Free Device</p>
<p>APM9948 J : <span style="border: 1px solid black; padding: 2px;">APM9948 XXXXX</span></p>	<p>XXXXX - Date Code</p>

Note: ANPEC lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. ANPEC lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020C for MSL classification at lead-free peak reflow temperature. ANPEC defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

**Absolute Maximum Ratings** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Rating	Unit	
$V_{DSS}$	Drain-Source Voltage	60	V	
$V_{GSS}$	Gate-Source Voltage	$\pm 20$		
$I_D^*$	Continuous Drain Current	4	A	
$I_{DM}^*$	300 $\mu\text{s}$ Pulsed Drain Current			
$I_S^*$	Diode Continuous Forward Current	2.5	A	
$T_J$	Maximum Junction Temperature	150	$^\circ\text{C}$	
$T_{STG}$	Storage Temperature Range	-55 to 150		
$P_D^*$	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	2.5	W
		$T_A=100^\circ\text{C}$	1	
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient	50	$^\circ\text{C}/\text{W}$	

Note:

\*Surface Mounted on 1in<sup>2</sup> pad area,  $t \leq 10\text{sec}$ .

**Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Test Condition	APM9948J			Unit
			Min.	Typ.	Max.	
<b>Static Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_{DS}=250\mu\text{A}$	60			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=48\text{V}, V_{GS}=0\text{V}$ $T_A=25^\circ\text{C}$			1	$\mu\text{A}$
					30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu\text{A}$	1	1.9	3	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 16\text{V}, V_{DS}=0\text{V}$			$\pm 10$	$\mu\text{A}$
$R_{DS(ON)}^a$	Drain-Source On-state Resistance	$V_{GS}=10\text{V}, I_{DS}=4\text{A}$		60	85	m $\Omega$
		$V_{GS}=4.5\text{V}, I_{DS}=3\text{A}$		72	100	
<b>Diode Characteristics</b>						
$V_{SD}^a$	Diode Forward Voltage	$I_{SD}=2.5\text{A}, V_{GS}=0\text{V}$		0.8	1.1	V
$t_{rr}$	Reverse Recovery Time	$I_{SD}=4\text{A}, dI_{SD}/dt=100\text{A}/\mu\text{s}$		28		ns
$Q_{rr}$	Reverse Recovery Charge			28		nC

**Electrical Characteristics (Cont.)** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

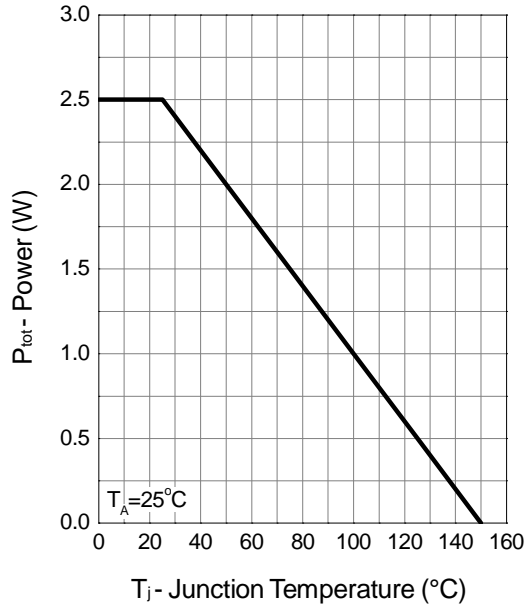
Symbol	Parameter	Test Condition	APM9948J			Unit
			Min.	Typ.	Max.	
<b>Dynamic Characteristics</b> <sup>b</sup>						
$R_G$	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		4.3		$\Omega$
$C_{iss}$	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=30V,$ Frequency=1.0MHz		610		pF
$C_{oss}$	Output Capacitance			47		
$C_{rss}$	Reverse Transfer Capacitance			30		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=30V, R_L=30\Omega,$ $I_{DS}=1A, V_{GEN}=10V,$ $R_G=6\Omega$		7	14	ns
$T_r$	Turn-on Rise Time			6	12	
$t_{d(OFF)}$	Turn-off Delay Time			26	48	
$T_f$	Turn-off Fall Time			4	8	
<b>Gate Charge Characteristics</b> <sup>b</sup>						
$Q_g$	Total Gate Charge	$V_{DS}=30V, V_{GS}=10V,$ $I_{DS}=4A$		14.2	20	nC
$Q_{gs}$	Gate-Source Charge			1.9		
$Q_{gd}$	Gate-Drain Charge			3.2		

## Notes:

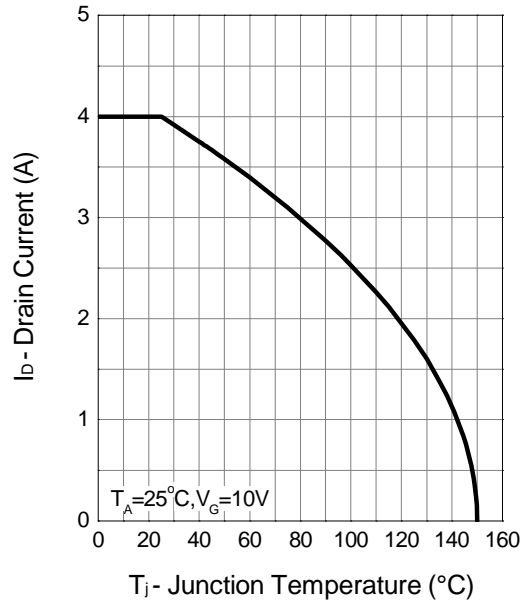
- a : Pulse test ; pulse width $\leq 300\mu\text{s}$ , duty cycle $\leq 2\%$ .  
 b : Guaranteed by design, not subject to production testing.

### Typical Characteristics

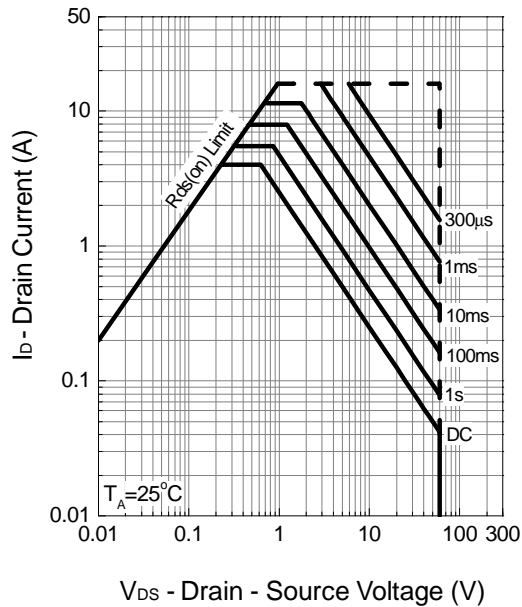
Power Dissipation



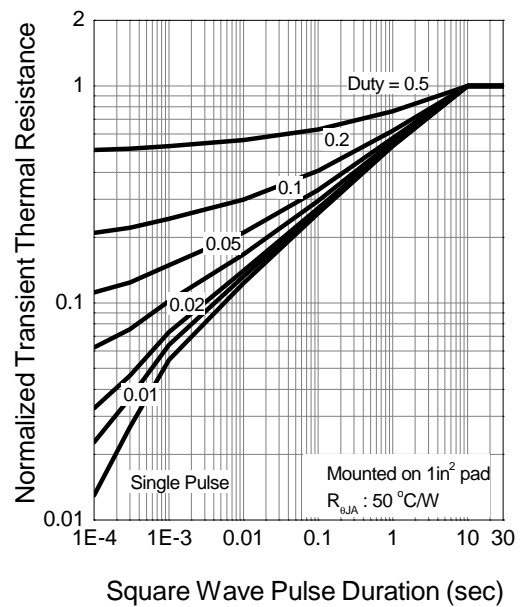
Drain Current



Safe Operation Area

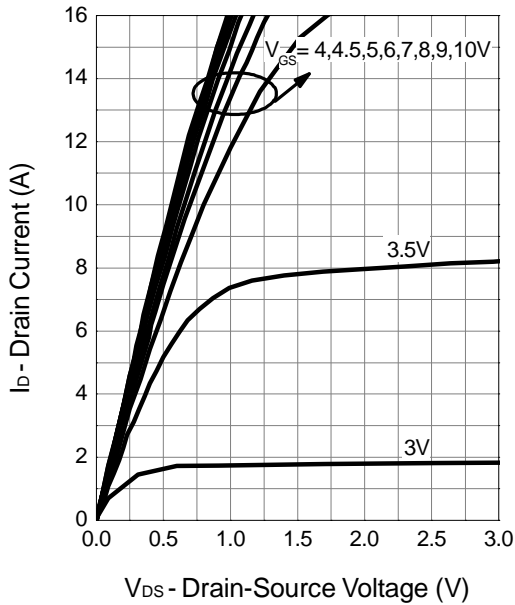


Thermal Transient Impedance

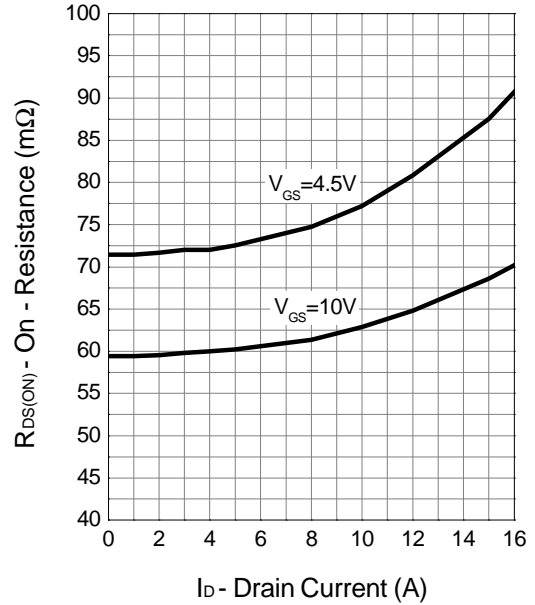


Typical Characteristics (Cont.)

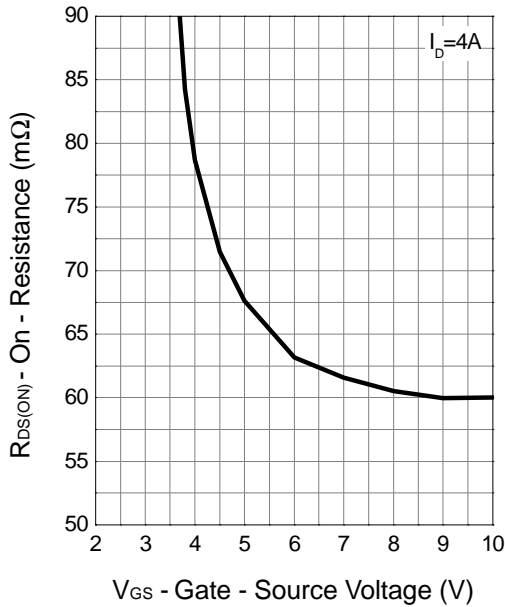
Output Characteristics



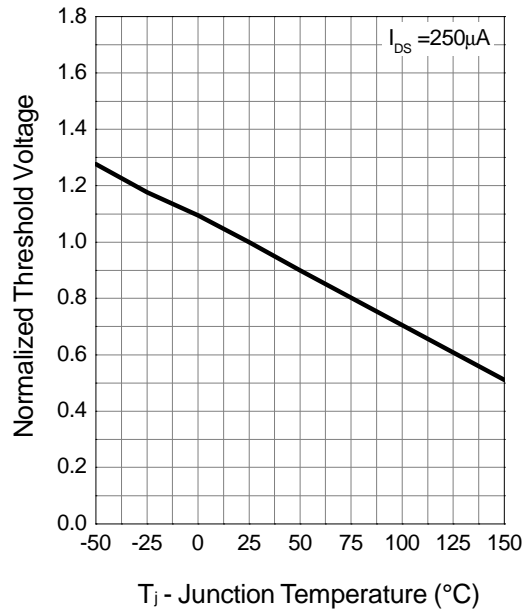
Drain-Source On Resistance



Drain-Source On Resistance

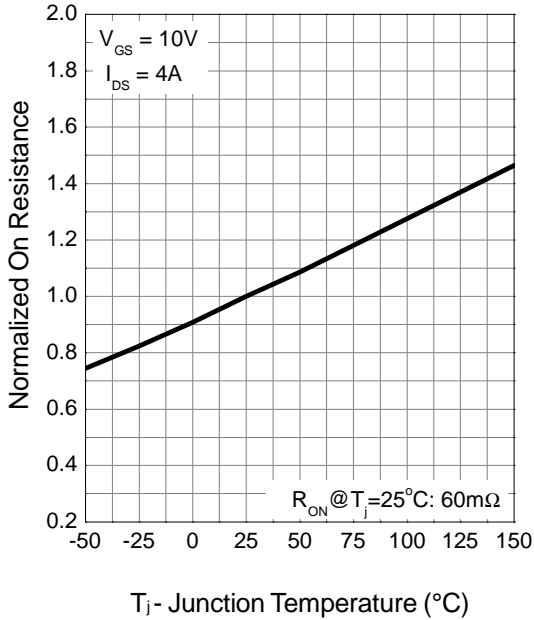


Gate Threshold Voltage

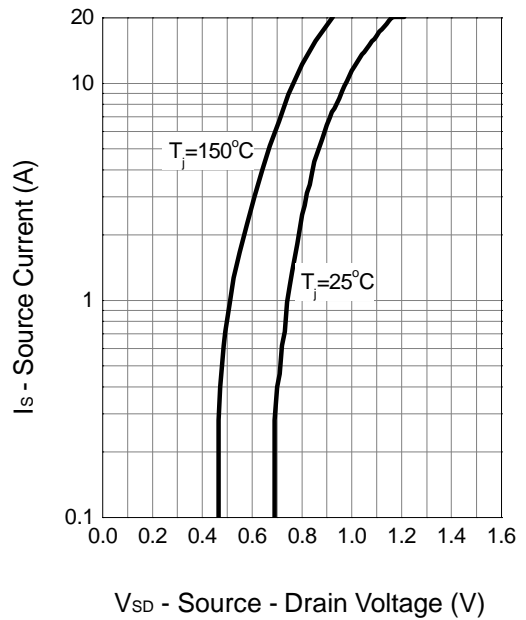


Typical Characteristics (Cont.)

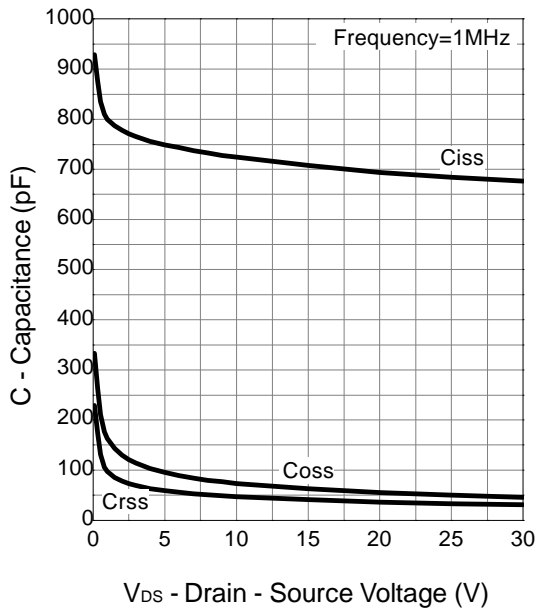
Drain-Source On Resistance



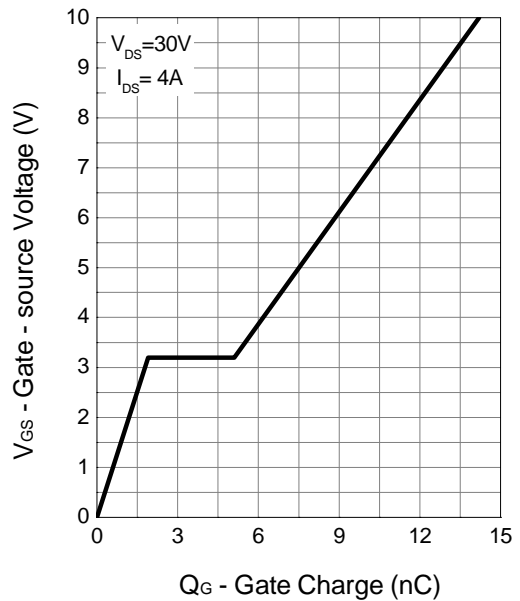
Source-Drain Diode Forward



Capacitance

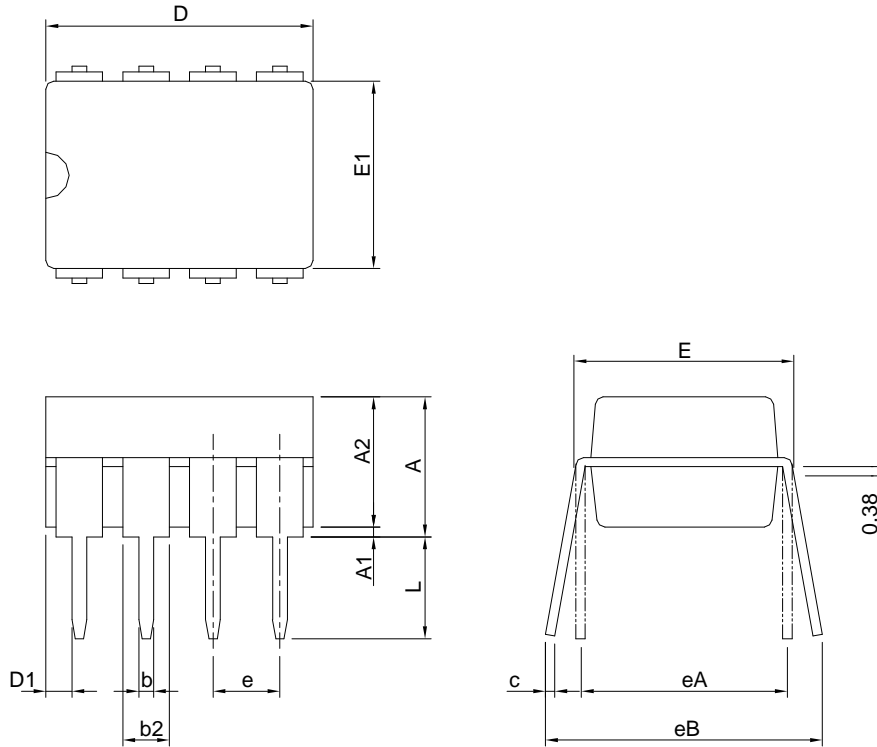


Gate Charge



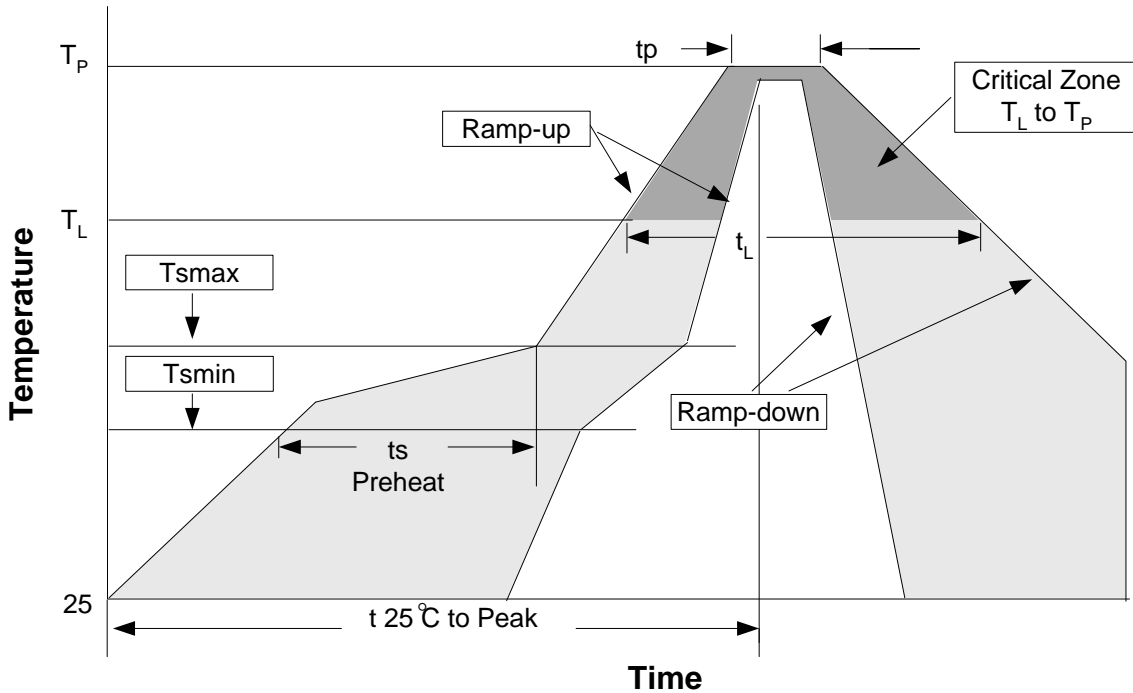
## Package Information

### DIP-8



DIMENSIONS	DIP-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A		5.33		0.210
A1	0.38		0.015	
A2	2.92	4.95	0.115	0.195
b	0.36	0.56	0.014	0.022
b2	1.14	1.78	0.045	0.070
c	0.20	0.35	0.008	0.014
D	9.01	10.16	0.355	0.400
D1	0.13		0.005	
E	7.62	8.26	0.300	0.325
E1	6.10	7.11	0.240	0.280
e	2.54 BSC		0.100 BSC	
eA	7.62 BSC		0.300 BSC	
eB		10.92		0.430
L	2.92	3.81	0.115	0.150

**Reflow Condition (IR/Convection or VPR Reflow)**



**Reliability Test Program**

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 sec
HOLT	MIL-STD-883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100%RH, 121°C
TST	MIL-STD-883D-1011.9	-65°C~150°C, 200 Cycles

**Classification Reflow Profiles**

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T <sub>L</sub> to T <sub>P</sub> )	3°C/second max.	3°C/second max.
Preheat		
- Temperature Min (T <sub>min</sub> )	100°C	150°C
- Temperature Max (T <sub>max</sub> )	150°C	200°C
- Time (min to max) (t <sub>s</sub> )	60-120 seconds	60-180 seconds
Time maintained above:		
- Temperature (T <sub>L</sub> )	183°C	217°C
- Time (t <sub>L</sub> )	60-150 seconds	60-150 seconds
Peak/Classification Temperature (T <sub>p</sub> )	See table 1	See table 2
Time within 5°C of actual Peak Temperature (t <sub>p</sub> )	10-30 seconds	20-40 seconds
Ramp-down Rate	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Note: All temperatures refer to topside of the package. Measured on the body surface.



## Classification Reflow Profiles (Cont.)

Table 1. SnPb Eutectic Process – Package Peak Reflow Temperatures

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> ≥350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5°C

Table 2. Pb-free Process – Package Classification Reflow Temperatures

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> 350-2000	Volume mm <sup>3</sup> >2000
<1.6 mm	260 +0°C*	260 +0°C*	260 +0°C*
1.6 mm – 2.5 mm	260 +0°C*	250 +0°C*	245 +0°C*
≥2.5 mm	250 +0°C*	245 +0°C*	245 +0°C*

\*Tolerance: The device manufacturer/supplier **shall** assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C. For example 260°C+0°C) at the rated MSL level.

## Customer Service

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